

RJK03E8DPA

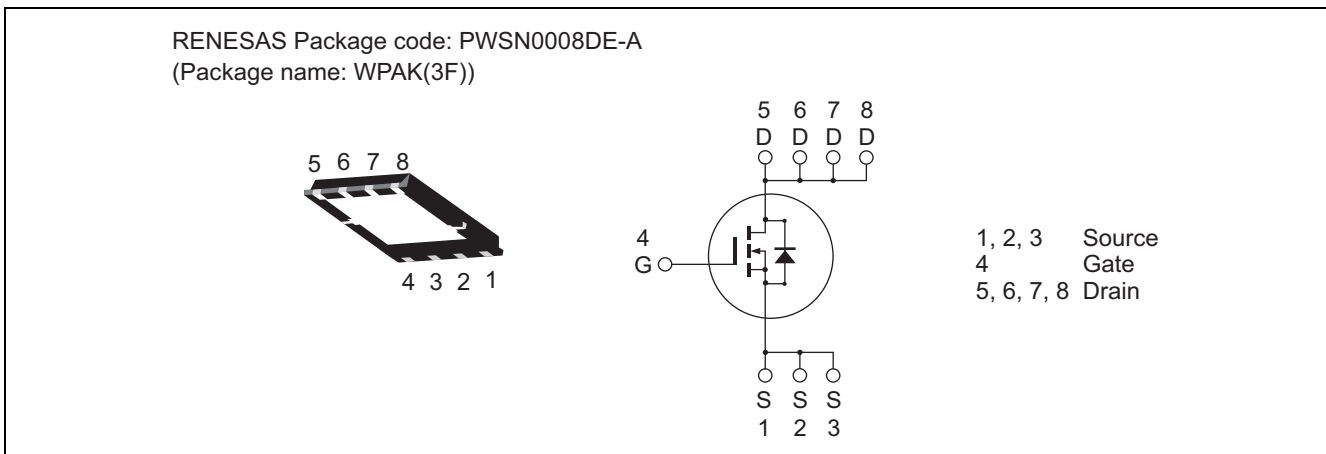
30V, 40A, 3.5mΩ max.
N Channel Power MOS FET
High Speed Power Switching

R07DS0934EJ0400
Rev.4.00
Mar 22, 2013

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- Pb-free
- Halogen-free

Outline



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±12	V
Drain current	I _D	40	A
Drain peak current	I _{D(pulse)} ^{Note1}	160	A
Body-drain diode reverse drain current	I _{DR}	40	A
Avalanche current	I _{AP} ^{Note 2}	18	A
Avalanche energy	E _{AR} ^{Note 2}	32.4	mJ
Channel dissipation	P _{ch} ^{Note3}	40	W
Channel to case thermal impedance	θ _{ch-c} ^{Note3}	3.13	°C/W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

- Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Value at T_{ch} = 25°C, R_g ≥ 50 Ω
3. T_c = 25°C

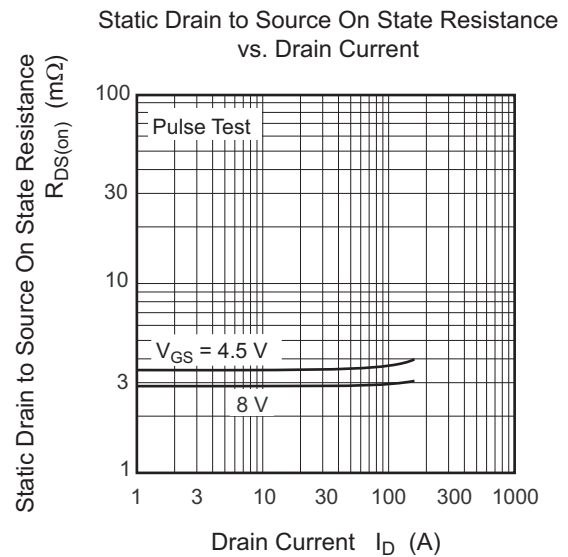
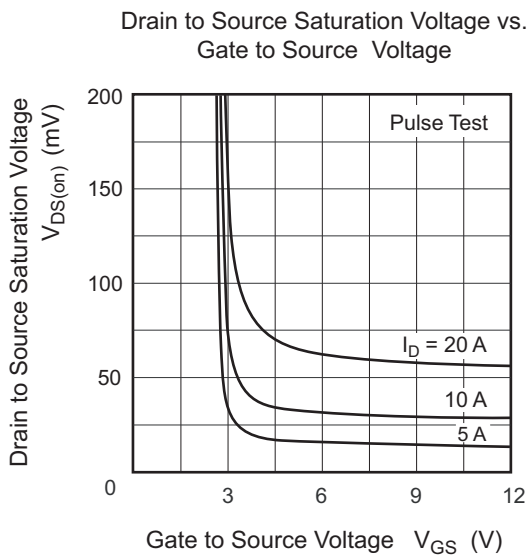
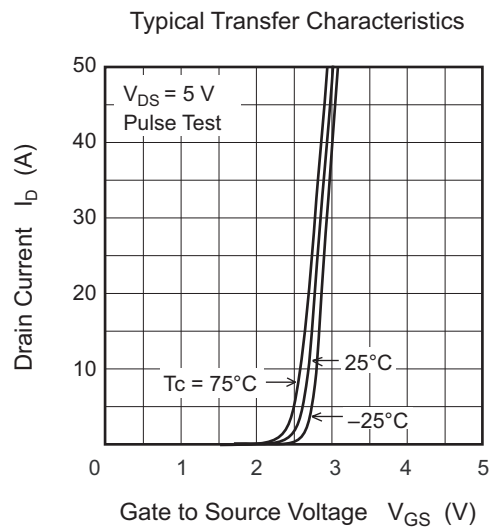
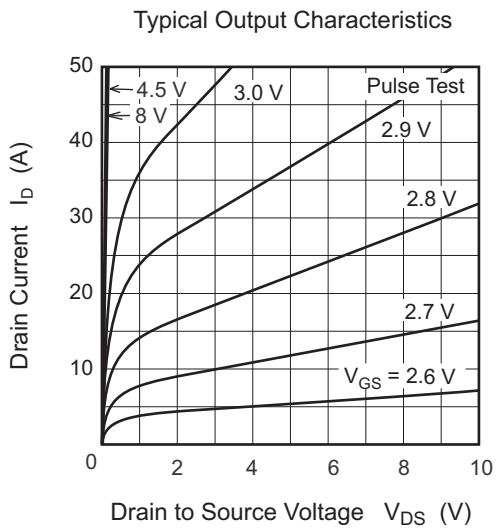
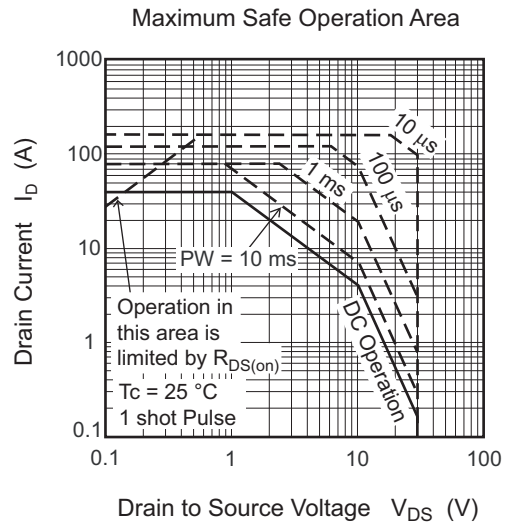
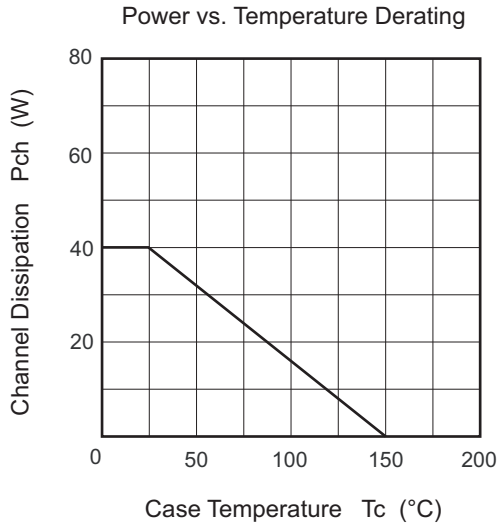
Electrical Characteristics

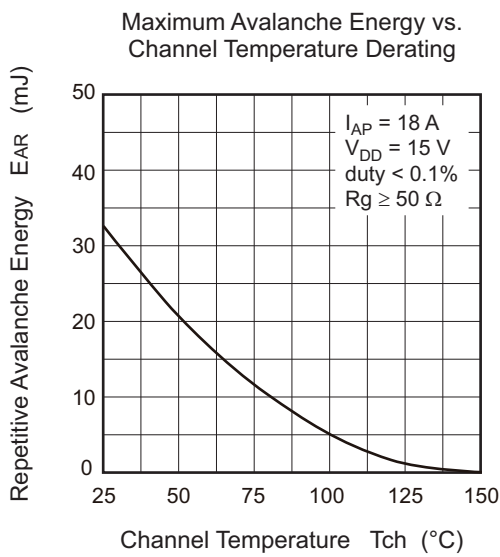
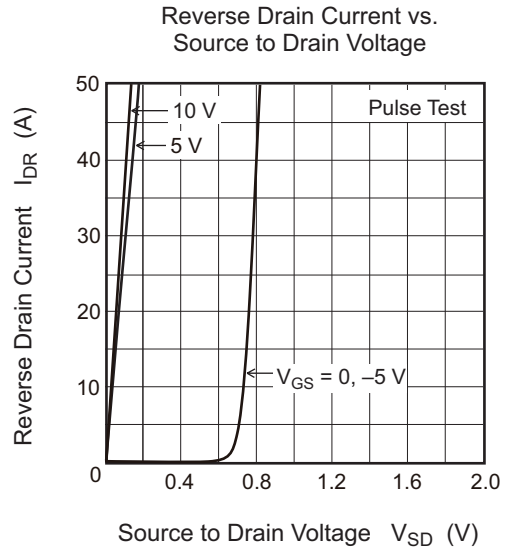
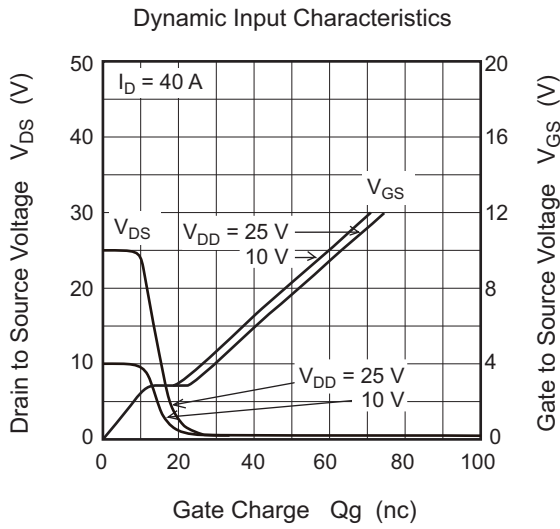
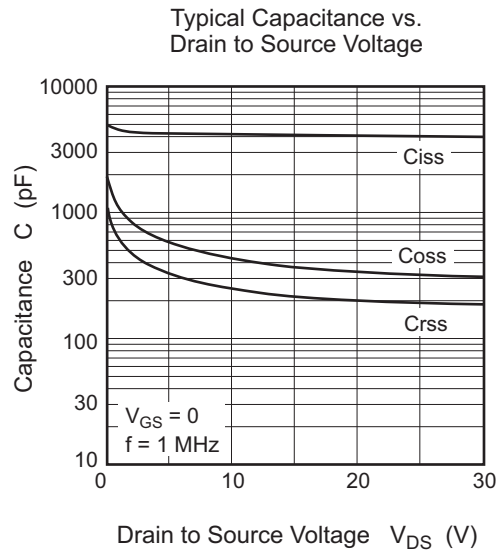
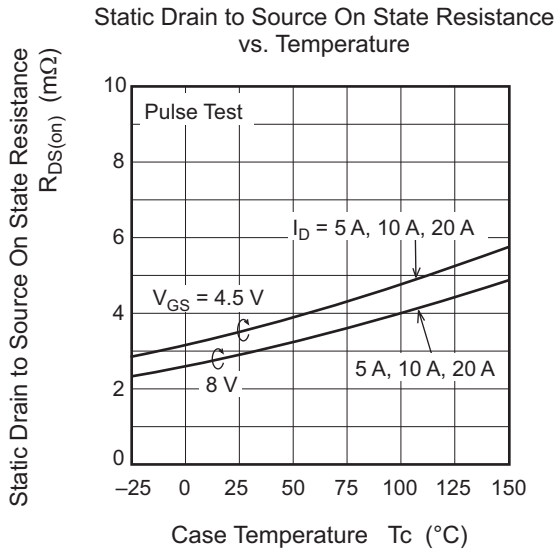
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 12 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.2	—	2.5	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	2.9	3.5	$\text{m}\Omega$	$I_D = 20 \text{ A}$, $V_{GS} = 8.0 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	3.5	4.4	$\text{m}\Omega$	$I_D = 20 \text{ A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	—	110	—	S	$I_D = 20 \text{ A}$, $V_{DS} = 5 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	4100	5740	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	430	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	250	—	pF	$f = 1 \text{ MHz}$
Gate Resistance	R_g	—	1.3	2.6	Ω	
Total gate charge	Q_g	—	28	—	nC	$V_{DD} = 10 \text{ V}$
Gate to source charge	Q_{gs}	—	13	—	nC	$V_{GS} = 4.5 \text{ V}$
Gate to drain charge	Q_{gd}	—	8.2	—	nC	$I_D = 40 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$V_{GS} = 8 \text{ V}$, $I_D = 20 \text{ A}$
Rise time	t_r	—	6.8	—	ns	$V_{DD} \cong 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	62	—	ns	$R_L = 0.5 \Omega$
Fall time	t_f	—	10	—	ns	$R_g = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	—	0.80	1.04	V	$I_F = 40 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	22	—	ns	$I_F = 40 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

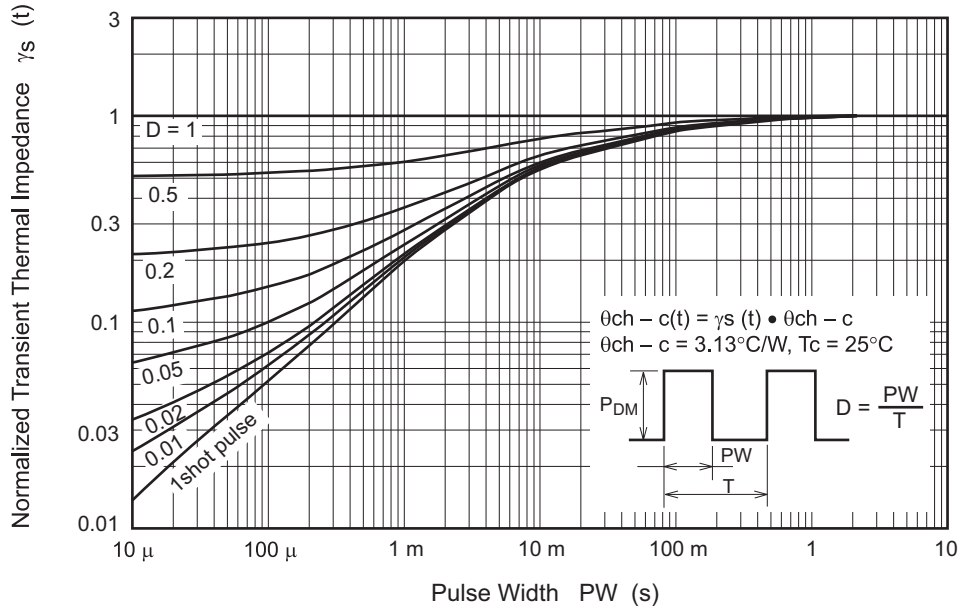
Notes: 4. Pulse test

Main Characteristics

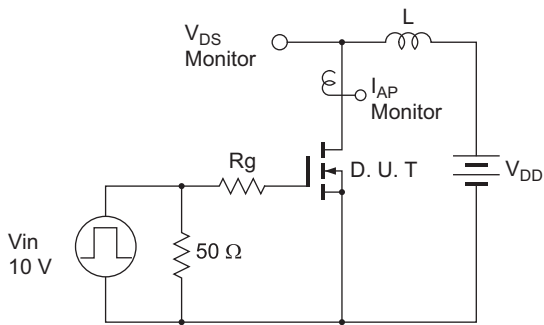




Normalized Transient Thermal Impedance vs. Pulse Width

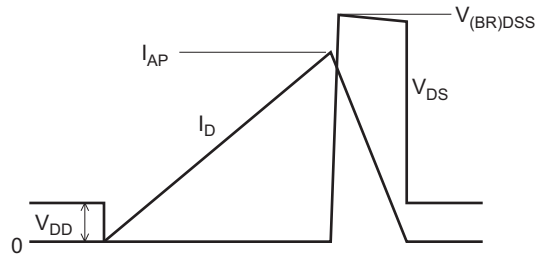


Avalanche Test Circuit

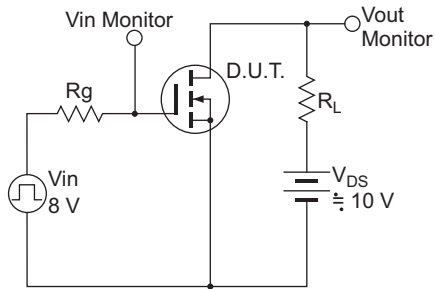


Avalanche Waveform

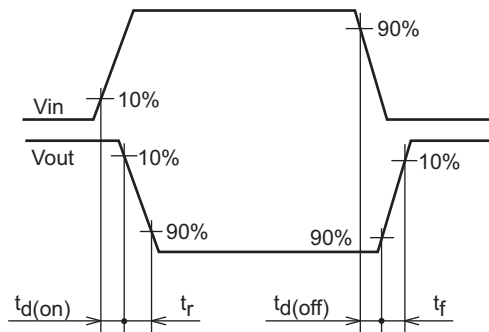
$$E_{AR} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



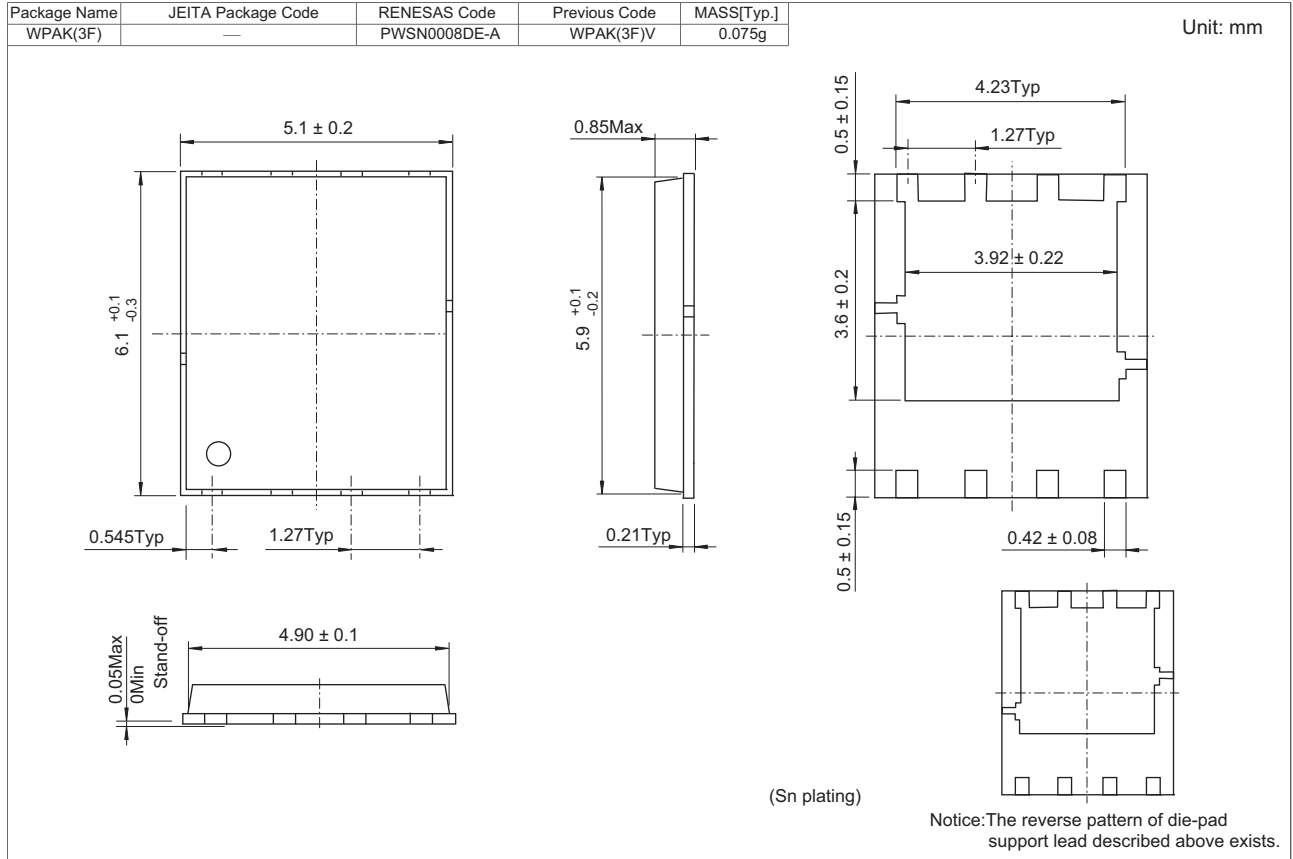
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJK03E8DPA-00-J5A	3000 pcs	Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

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